

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet

1

of

1

**Complete if Known**

Application Number

**To Be Assigned**

101796672

Filing Date

Concurrently Herewith

319/2004

**First Named Inventor**

Young-pil Kim et al

### Group Art Unit

Unknown

2015

**Examiner Name**

UNKNOWN

London

Attorney Docket Number

5649-1276

## U.S. PATENTS AND PATENT PUBLICATIONS

[illegible]

**FOREIGN PATENT DOCUMENTS**

[illegible]

## OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
<i>ML</i>	1	Young Pil Kim et al., "Reliability Degradation of High Density DRAM Cell Transistor Junction Leakage Current Induced by Band-to-Defect tunneling Under the Off-State Bias-Temperature Stress," <u>IEEE</u> , 2001	
<i>ML</i>	2	K. Saino et al., "Impact of Gate-Induced Drain Leakage Current on the Tail Distribution of DRAM Data Retention Time," <u>IEEE</u> , 2000	

**Examiner Signature**

Matthew C. Lamber

Date Considered

7/15/06

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.